

GAN-BASED RADIATION-EMITTING THIN-LAYERED SEMICONDUCTOR COMPONENT

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Cited documents:

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US6346771

WO0141225

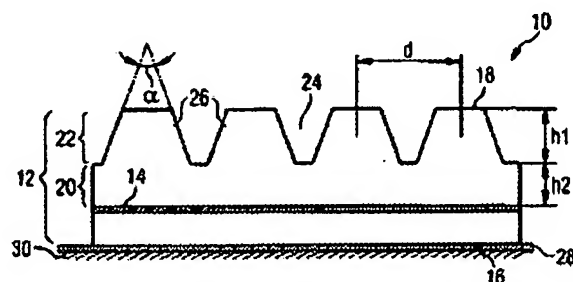
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Abstract of WO2004017430

The invention relates to a radiation-emitting thin-layered semiconductor component comprising a GaN-based multilayer structure (12) that is provided with an active, radiation-generating layer (14), a first main area (16), and a second main area (18) that is located opposite the first main area and decouples the radiation generated in the active, radiation-generating layer. The first main area (16) of the multilayer structure (12) is coupled to a reflective layer or border area while the region (22) of the multilayer structure, which borders the second main area (18) thereof, is structured in a one-dimensional or two-dimensional manner and is provided with convex elevations (26).



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